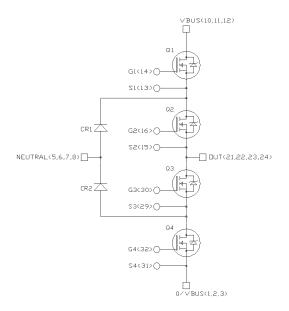
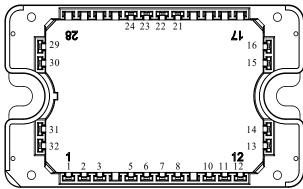
MSCSM170TLM45C3AG

Three Level Inverter SiC MOSFET Power Module

Product Overview

The MSCSM170TLM45C3AG device is a three level inverter 1700V/64A silicon carbide (SiC) MOSFET power module.





Notes:

- 1. All multiple inputs and outputs must be shorted together. 1/2/3; 10/11/12; 5/6/7/8; 21/22/23/24.
- 2. All ratings at T_J = 25 °C, unless otherwise specified.

⚠ CAUTION

These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are key features of the MSCSM170TLM45C3AG device:

- · SiC Power MOSFET
 - Low R_{DS(on)}
 - High temperature performance
- SiC Schottky Diode (CR1 and CR2)
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on VF
- · Low stray inductance
- Kelvin source for easy drive
- · High level of integration
- · Aluminum nitride (AIN) substrate for improved thermal performance

Benefits

The following are the benefits of MSCSM170TLM45C3AG device:

- · Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals for power and signal for easy mounting of PCB mounting
- Low profile
- **RoHS Compliant**

Application

The MSCSM170TLM45C3AG device is designed for the following applications:

· Uninterruptible power supplies

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Electrical Specifications

This section provides the electrical specifications of the MSCSM170TLM45C3AG device.

SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM170TLM45C3AG device.

Table 1. Absolute Maximum Ratings

Symbol	Parameter	Parameter		Unit
V _{DSS}	Drain-Source voltage		1700	V
I _D	Continuous drain current	Continuous drain current $T_C = 25 ^{\circ}\text{C}$ $T_C = 80 ^{\circ}\text{C}$		Α
I _{DM}	Pulsed drain current	Pulsed drain current		
V _{GS}	Gate-Source voltage	Gate-Source voltage		V
R _{DS(on)}	Drain-Source ON resistance	Drain-Source ON resistance		mΩ
P _D	Power dissipation	T _C = 25 °C	319	W

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM170TLM45C3AG device.

Table 2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0V; V _{DS} = 1700V		_	10	100	μΑ
R _{DS(on)}	Drain-Source on	V _{GS} = 20V	T _J = 25 °C	_	35	45	mΩ
	resistance	I _D = 30A	T _J = 175 °C	_	62	_	
V _{GS(th)}	Gate threshold voltage	$V_{GS} = V_{DS}$; $I_D = 2.5 \text{ mA}$		1.8	3.2	_	V
I _{GSS}	Gate–Source leakage current	$V_{GS} = 20V; V_{DS} = 0V$		_	_	150	nA

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM170TLM45C3AG device.

Table 3. Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	V _{GS} = 0V		_	3300	_	pF
C _{oss}	Output capacitance	V _{DS} = 1000V		_	150	_	
C _{rss}	Reverse transfer capacitance	f = 1 MHz		_	10	_	
Qg	Total gate charge	V _{GS} = -5V/20V		_	178	_	nC
Q _{gs}	Gate-source charge	V _{Bus} = 850V		_	49	_	
Q_{gd}	Gate-drain charge	I _D = 30A		_	27	_	
T _{d(on)}	Turn-on delay time	V _{GS} = -5V/20V	T _J = 150 °C	_	24	_	ns
T _r	Rise time	V _{Bus} = 900V		_	17	_	
T _{d(off)}	Turn-off delay time	I _D = 50A		_	35	_	
T _f	Fall time	$R_{G(on)} = 4.7\Omega$ $R_{G(off)} = 2.7\Omega$			19	_	
Eon	Turn-on energy	V _{GS} = -5V/20V	T _J = 150 °C	_	1.1	_	mJ
E _{off}	Turn-off energy	$V_{Bus} = 900V$ $I_D = 50A$ $R_{G(on)} = 4.7\Omega$ $R_{G(off)} = 2.7\Omega$	T _J = 150 °C	_	0.16	_	
R _{Gint}	Internal gate resistance	ance			0.85	_	Ω
R _{thJC}	Junction-to-case therm	al resistance		_	_	0.47	°C/W

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM170TLM45C3AG device.

Table 4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{SD}	Diode forward voltage	$V_{GS} = 0V; I_{SD} = 30A$	_	3.7	_	V
		$V_{GS} = -5V; I_{SD} = 30A$	_	3.9	_	
t _{rr}	Reverse recovery time	$I_{SD} = 30A; V_{GS} = -5V$	_	27	_	ns
Q _{rr}	Reverse recovery charge	$V_R = 900V$; $di_F/dt = 1000 A/\mu s$	_	650	_	nC
I _{rr}	Reverse recovery current		_	46	_	Α

CR1 and CR2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the CR1 and CR2 SiC diode ratings and characteristics per SiC diode of MSCSM170TLM45C3AG device.

Table 5. SiC Schottky Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
V _{RRM}	Peak repetitive reverse volta	age		_	_	1700	V
I _{RRM}	Reverse leakage current	V _R = 1700V	T _J = 25 °C	_	10	200	μA
			T _J = 175 °C	_	150	_	
I _F	DC forward current	_	T _C = 125 °C	_	30	_	Α
V _F	Diode forward voltage	I _F = 30A	T _J = 25 °C	_	1.5	1.8	V
			T _J = 175 °C	_	2.3	_	
Q _C	Total capacitive charge	V _R = 900V		_	230	_	nC
С	Total capacitance	$f = 1 \text{ MHz}, V_R = 600V$ $f = 1 \text{ MHz}, V_R = 900V$		_	167	_	pF
				_	138	_	
R _{thJC}	Junction-to-case thermal re-	sistance		_	_	0.52	°C/W

Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM170TLM45C3AG device.

Table 6. Thermal and Package Characteristics

Symbol	Characteristics	Min.	Max.	Unit		
V _{ISOL}	RMS isolation voltage, any terminal to c	ase t =1 min, 5	50 Hz/60 Hz	4000	_	V
T _J	Operating junction temperature range			-40	175	°C
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _{Jmax} –25	
T _{STG}	Storage temperature range				125	
T _C	Operating case temperature			-40	125	
Torque	Mounting torque	2	3	N.m		
Wt	Package weight			_	110	g

Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM170TLM45C3AG device.

Figure 1. Maximum Thermal Impedance

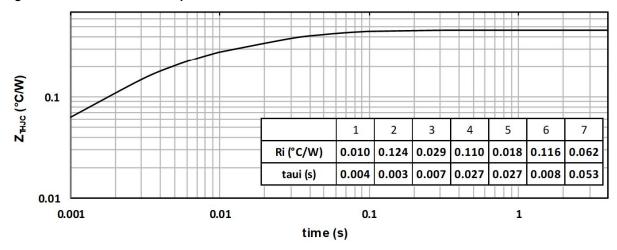


Figure 2. Output Characteristics, T_J = 25 °C

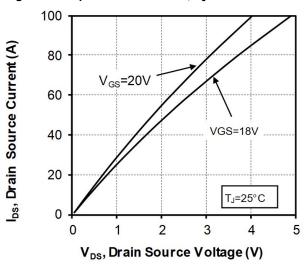


Figure 3. Output Characteristics, T_J = 175 °C

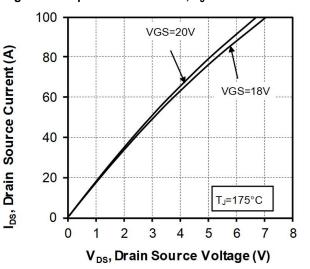


Figure 4. Normalized R_{DS(on)} vs. Temperature

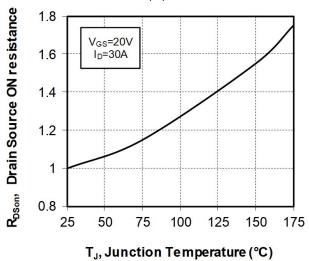


Figure 5. Transfer Characteristics

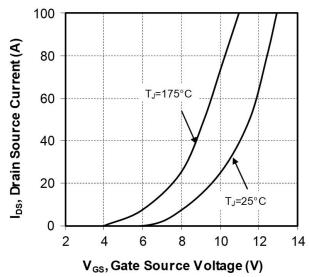


Figure 6. Switching Energy vs. Rg

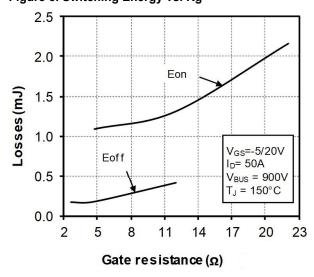


Figure 7. Switching Energy vs. Current

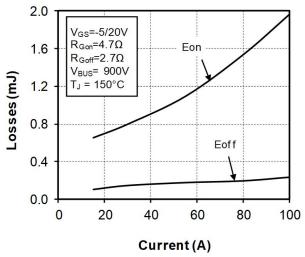


Figure 8. Capacitance vs. Drain Source Voltage

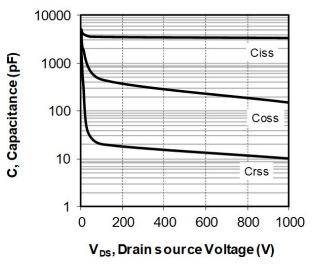


Figure 9. Gate Charge vs. Gate Source Voltage

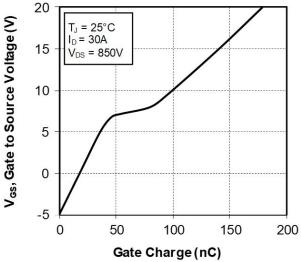


Figure 10. Body Diode Characteristics, T_J = 25 °C

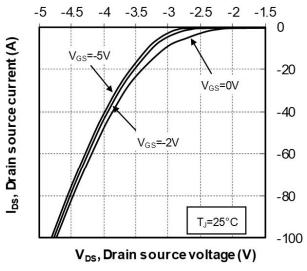
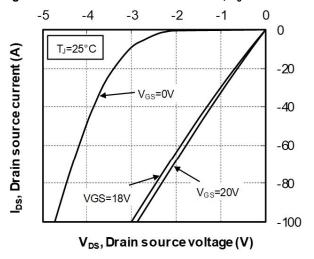


Figure 11. 3rd Quadrant Characteristics, T_J = 25 °C



-80

-100

Figure 12. Body Diode Characteristics, T_J = 175 °C Figure 13. 3rd Quadrant Characteristics, T_J = 175 °C -4.5 -4 -3.5 -3 -2.5 -2 -1.5 -1 los, Drain source current (A) Drain source current (A) V_{GS}=-5V -20 V_{GS}=-2V -40 V_{GS}=0V -60 -80 los, T_J=175°C

V_{DS}, Drain source voltage (V)

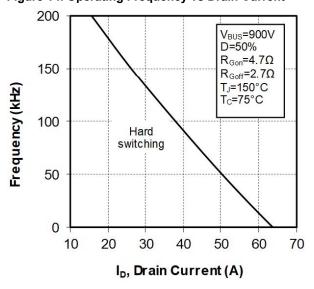
-100

0 T_J=175°C -20 -40 V_{GS}=20V VGS=18V -60

V_{DS}, Drain source voltage (V)

V_{GS}=0V

Figure 14. Operating Frequency vs Drain Current



Typical SiC Diode Performance Curves

This section shows the typical SiC diode performance curves of the MSCSM170TLM45C3AG device.

Figure 15. Maximum Thermal Impedance

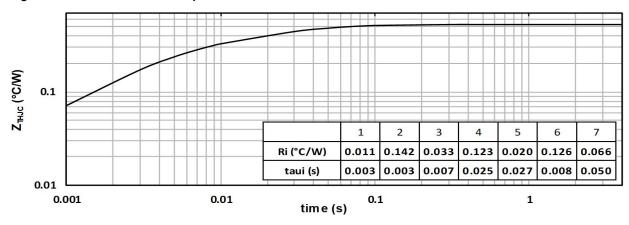


Figure 16. Forward Characteristics

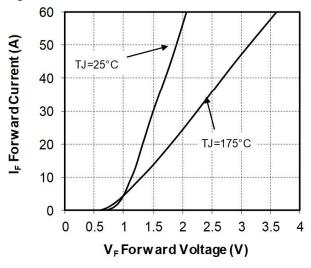
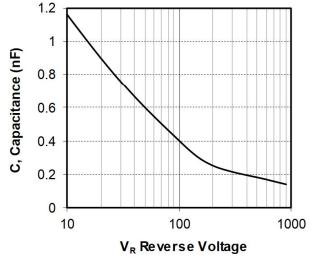


Figure 17. Capacitance vs. Reverse Voltage



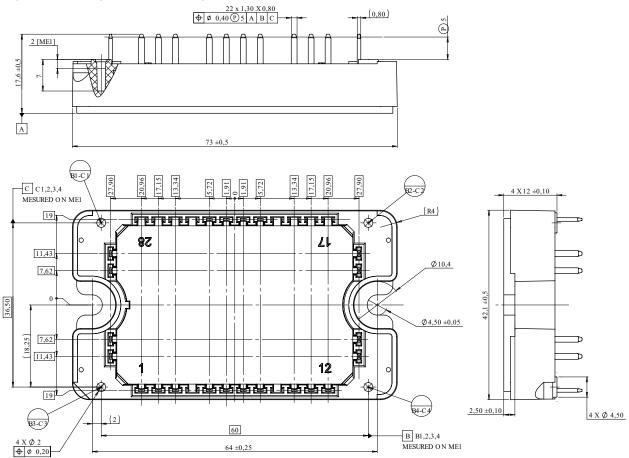
Package Specifications

The following section shows the package specification of the MSCSM170TLM45C3AG device.

Package Outline

The following figure shows the package outline drawing of the MSCSM170TLM45C3AG device. The dimensions in the following figure are in millimeters.

Figure 18. Package Outline Drawing



Note: See AN3500A—Mounting Instructions for SP1F and SP3F Power Modules for more information...

Revision History

Revision	Date	Description
Α	12/2021	This is the first publication of this document.

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